

Abstract of the Disclosure

A titanium layer is formed on a substrate with chemical vapor deposition (CVD). First, a seed layer is formed on the substrate by combining a first precursor with a reducing agent by CVD. Then, the titanium layer is formed on the substrate by  
5 combining a second precursor with the seed layer by CVD. The titanium layer is used to form contacts to active areas of substrate and for the formation of interlevel vias.

"Express Mail" mailing label number: EL873860197US

Date of Deposit: August 28, 2001

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09041123 002201  
T082200 E2T4660